

Amendments to the Title:

METHODS AND APPARATUS RELATING TO SINGULATING SEMICONDUCTOR
WAFERS AND WAFER SCALE ASSEMBLIES

Amendments to the Specification:

Please replace paragraph number [0007] with the following:

[0007] An alternative method of dicing is disclosed in U.S. Patent No. 6,136,688 to Tamaki et al. Using this technique a metal layer in the form of a grid extending over the streets is formed over an active surface of a silicon wafer. The silicon wafer body is singulated, but for the presence of the metal layer, by etching therethrough (after back grinding to reduce the wafer thickness) from the back side to the metal layer. The dice are then separated by melting and fusing the metal layer along the streets using a laser. Since this method involves etching through the entire thickness of the wafer and requires the presence of the metal layer as well as enough separation from the integrated circuitry of each semiconductor die to avoid damage from the laser-fused metal, the required width of the streets remains significant. This method also requires the extra steps to form the metal layer.